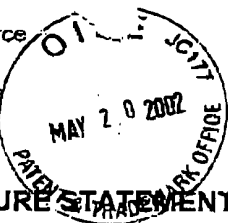


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F00-219-US-DIV-3

Applicant: MANABE et al.

Appln. No.: 09/677,781

Filing Date: October 2, 2000

Date: May 20, 2002

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Examiner: S. MULPURI

Group Art Unit: 2812

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					Enclosed No	Enclose No
Sm	FR 58-200527	11/1983	Japan		X	
Sm	GR 60-175468	09/1985	Japan		X	
Sm	HR 63-188938	08/1988	Japan		X	
Sm	IR 02-042770	02/1990	Japan		X	
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	PR	HIRAMATSU, K., "Effects of Buffer Layer in MOCVD Growth of GaN Film on Sapphire Substrate," <i>Nagoya University</i> , 1988, pp. 334-342.			DUPLICATE
	QR	KHAN M., "Effect of Si on Photoluminescence of GaN," <i>Solid State Communications</i> , Vol. 57, No. 6, 1986, pp. 405-409.			
	RR	SZE, S., "Physics of Semiconductor Devices," <i>Wiley-Interscience</i> , 1969, pp. 42-43.			
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	UR				
	VR				
	WR				

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Date Considered:

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.

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Examiner: S. Mulpuri

Group Art Unit: 2812

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LR	56-080183	07/1981	Japan	Kobayashi et al.	X	
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GM	XR	Sayyah, A Study of Growth Mechanisms and Electrical and Optical Properties of Epitaxial Al _x Ga _{1-x} N layers Grown by Atmospheric Pressure Metalorganic Chemical Vapor Deposition, Dissertation for University of Southern California, pp. 1-176, February 1986		

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Date Considered: 12/9/03

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Div. of Appln. No.: 09/417,778

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Examiner: Minh Loan Tran

Group Art Unit: 2811

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							Enclosed	No	Enclose	No
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	PR 2-275682	11/1990	Japan					X		X
	QR 5-042785	04/1975	Japan					X		X
	RR 59-228776	12/1994	Japan					X		X
	SR 0 620 203 A1	10/1994	Europe	Nakahata				X		X
	TR 0-277597	08/1988	EPA					X		X
	UR 03-034549	02/1991	Japan	Toyoda				X		X
	VR 34549	02/1991	Japan	Hatano				X		X
	WR 4,006,449	09/1990	Germany	Manabe				X		X
SM	XR 57-018377	01/1982	Japan	KOBAYASHI				X		X

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	ZR	J. Akasaki et al., "Effects of AlN Buffer Layer on Crystallographic Structure... by MOVPE", J. Crystal Growth 98 (1989) pp. 209-19.			
	AAR	Liu et al., "Growth morphology and surface-acoustic-wave measurements of AlN films on Sapphire," Journal of Applied Physics, Vol. 46, No. 9, September 1975, pages 3703-3706.			
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Examiner

Date Considered: 6/26/01

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							Enclosed	No	Enclose	No
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	NR 61-007671	01/1986	Japan	Kawabata				X		X
	OR 57-087184	05/1982	Japan	Tabuchi				X		X
	PR 57-153479	09/1982	Japan	Ooki				X		X
	QR 2-738329	03/1978	Germany	Jacob et al.				X		X
	RR 56-59699	05/1981	Japan	Ooki				X		X
	SR 34549	02/1991	Japan	Hatano				X		X
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	WR	Bottka, et al., Silicon and beryllium doping of OMVPE Grown..., Journal of Crystal Growth 68 (1984) pp. 54-59, North-Holland Amsterdam								
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Date Considered: 6/26/00

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

Applicant: MANABE et al.

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							Enclosed	No	Enclose	No
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	NR 2623466	2/1990	Japan	Sassa et al.				X		X
	OR 59-228776	6/1983	Japan	Maefutsu et al.				X		X
	PR 60-173829	2/1984	Japan	Maefutsu et al.				X		X
	QR 1-589351	05/1981	England							
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SM	UR 03-034549	02/1991	Japan							
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SM	WR	English Abstract of OOKI Japanese Application Published 9/19/82 under No. 57-153479.								
	XR	I. Akusuki et al., "Effects of AlN Buffer Layer on Crystallographic Structure... by MOVPE", J. Crystal Growth 98 (1989) pp. 209-19.								
	YR	Sayyah, A Study of Growth Mechanisms and Electrical and Optical Properties of Epitaxial Al _x Ga _{1-x} N Layers Grown by Atmospheric Pressure Metalorganic Chemical Vapor Deposition, A Dissertation presented to Faculty of the Graduate School, University of Southern California, February 1986, pp. 125-136.								
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Date Considered: 6/26/01

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	KR					
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		Document Number	Date MM/YYYY	Country	Inventor Name	Class	SubClass	Enclosed	No	Enclose	No
SM	MR	58-046686	03/1983	Japan	Yoneda				x		x
	NR	54-071590	06/1979	Japan	Toyoda				x		x
	OR	02-081482	03/1990	Japan	Manabe				x		x
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SN	BBR	Elwell et al. "Crystal Growth of Gallium Nitride" Prog. Crystal Growth and Charact. 1988, vol. 17, pp. 53-78.
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